ABSTRACT OF THE DISCLOSURE

A thin film depositing method comprising placing a substrate in a heating chamber; allowing a first gas to flow inside the heating chamber to heat the substrate through heat exchange with the first gas; moving the substrate to a deposition chamber, evacuating the deposition chamber, and then supplying a second gas into the deposition chamber; and causing an electrical discharge in the second gas such that the second gas decomposes into decomposition components and the decomposition components adhere to a substrate surface to deposit a film thereon, wherein the first gas is a gas from which moisture and organic substances have been removed. The time required for depositing thin films is reduced thereby improving the throughput, increases in apparatus costs are suppressed, and a thin film having good properties is obtained. A thin film depositing apparatus is also provided.